

# APPLICATION DATA SHEET

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Application Type: utility

Title of Invention: METHOD OF PREVENTING LEAKAGE CURRENT OF A METAL-OXIDE SEMICONDUCTOR TRANSISTOR

Customer Number Attorney: 027765



Customer Number Correspondence Address: 027765



## Continuity Data:

This application is a continuation in part of 09/683,691 2002-02-04 US pending

## Foreign Priority:

09/683,691 US 2002-02-04 Priority Claimed

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